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Si APD (to 1 μ m)

NIR Type (Low Bias
Operation)

NIR Type (Low Tem.
Coefficient)

Short Wavelength Type

NIR High Sensitivity Type

Surface-mount Type

Multi-element Type

NIR High Sensitivity Type

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Type No.	Active Area	Spectral Response Range	Peak Wavelength	Breakdown Voltage	Temperature Coefficient of VBR	Package Feature
S8890-02	dia.0.2 mm	400 to 1100 nm	940 nm	500 V	2.5 V/deg. C	TO-5
S8890-05	dia.0.5 mm	400 to 1100 nm	940 nm	500 V	2.5 V/deg. C	TO-5
S8890-10	dia.1 mm	400 to 1100 nm	940 nm	500 V	2.5 V/deg. C	TO-5
S8890-15	dia.1.5 mm	400 to 1100 nm	940 nm	500 V	2.5 V/deg. C	TO-5
S8890-30	dia.3 mm	400 to 1100 nm	940 nm	500 V	2.5 V/deg. C	TO-8
S9251-02	dia.0.2 mm	440 to 1100 nm	860 nm	250 V	1.85 V/deg. C	TO-18
S9251-05	dia.0.5 mm	440 to 1100 nm	860 nm	250 V	1.85 V/deg. C	TO-18
S9251-10	dia.1 mm	440 to 1100 nm	860 nm	250 V	1.85 V/deg. C	TO-5
S9251-15	dia.1.5 mm	440 to 1100 nm	860 nm	250 V	1.85 V/deg. C	TO-5

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